

Wolfspeed SiC and GaN Materials



RENEWABLE
ENERGY



BASE STATIONS
TELECOM



TRACTION



INDUSTRIAL MOTOR
CONTROL



POWER
MANAGEMENT



AUTOMOTIVE

Industry-Leading Portfolio, Innovation and Scale

UNPRECEDENTED PERFORMANCE & SCALE

With more than 30 years of development and manufacturing experience, Wolfspeed is driving innovation with the industry's broadest range of SiC and GaN materials. Delivering substrate and epitaxy options up to 150mm diameter, Wolfspeed provides a vertically integrated materials product offering that combines industry-leading volume, scale, quality and a vast intellectual property portfolio.

When you partner with Wolfspeed, you get the best and most innovative materials.

MATERIALS PORTFOLIO

Supported Diameters

- 100 mm
- 150 mm

SiC Substrates

- n-type
- High Purity SI

SiC Epitaxy

- n-type
- p-type
- Thick epitaxy

GaN Epitaxy

- GaN, AlN, AlGaIn
- AlInN, SiN layers
- HEMT structures

Learn how Wolfspeed can revolutionize your designs at wolfspeed.com/materials or contact us at materials_sales@wolfspeed.com or +1.919.313.5300.

Our materials are ISO-TS 16949 certified. The information in this document is subject to change without notice. Document revised February 15, 2019. © 2019 Cree, Inc. All rights reserved. Wolfspeed™ and the Wolfspeed logo are trademarks of Cree, Inc.


Wolfspeed
A CREE COMPANY

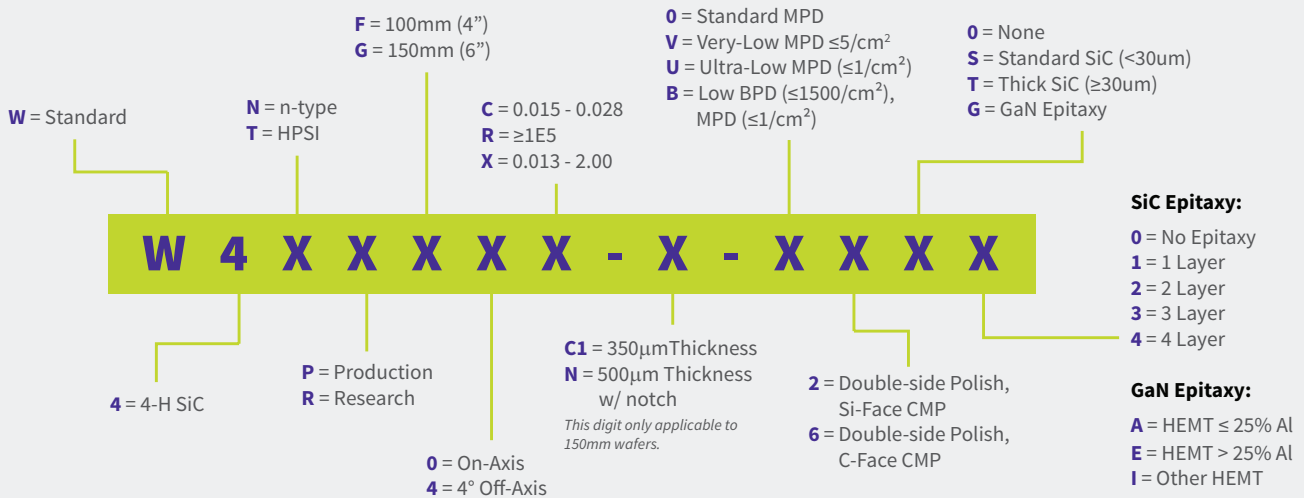
N-TYPE SiC SUBSTRATE PRODUCT DESCRIPTIONS

Part Number	Description
W4NRF4C-V200	4H-SiC, n-type, Research Grade, 100mm, 4° Off-Axis, 0.015-0.028 ohm-cm, Very Low MPD $\leq 5/cm^2$, 350um Thick w/ 32.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4NPF4C-V200	4H-SiC, n-type, Production Grade, 100mm, 4° Off-Axis, 0.015-0.028 ohm-cm, Very Low MPD $\leq 5/cm^2$, 350um Thick w/ 32.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4NRF4C-U200	4H-SiC, n-type, Research Grade, 100mm, 4° Off-Axis, 0.015-0.028 ohm-cm, Ultra Low MPD $\leq 1/cm^2$, 350um Thick w/ 32.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4NPF4C-U200	4H-SiC, n-type, Production Grade, 100mm, 4° Off-Axis, 0.015-0.028 ohm-cm, Ultra Low MPD $\leq 1/cm^2$, 350um Thick, w/ 32.5mm Flat Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4NPF4C-B200	4H-SiC, n-type, Production Grade, 100mm, 4° Off-Axis, 0.015-0.028 ohm-cm, Ultra Low MPD $\leq 1/cm^2$, Low BPD $\leq 1500/cm^2$, 350um Thick w/ 32.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4NRG4C-C1-V200	4H-SiC, n-type, Research Grade, 150mm, 4° Off-Axis, 0.015-0.028 ohm-cm, Very Low MPD $\leq 5/cm^2$, 350um Thick w/ 47.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4NPG4C-C1-V200	4H-SiC, n-type, Production Grade, 150mm, 4° Off-Axis, 0.015-0.028 ohm-cm, Very Low MPD $\leq 5/cm^2$, 350um Thick w/ 47.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4NRG4C-C1-U200	4H-SiC, n-type, Research Grade, 150mm, 4° Off-Axis, 0.015-0.028 ohm-cm, Ultra Low MPD $\leq 1/cm^2$, 350um Thick w/ 47.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4NPG4C-C1-U200	4H-SiC, n-type, Production Grade, 150mm, 4° Off-Axis, 0.015-0.028 ohm-cm, Ultra Low MPD $\leq 1/cm^2$, 350um Thick w/ 47.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4NPG4C-C1-B200	4H-SiC, n-type, Production Grade, 150mm, 4° Off-Axis, 0.015-0.028 ohm-cm, Ultra Low MPD $\leq 1/cm^2$, Low BPD $\leq 1500/cm^2$, 350um Thick w/ 47.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate

HIGH PURITY SEMI-INSULATING SiC SUBSTRATE PRODUCT DESCRIPTIONS

Part Number	Description
W4TRFOR-0200	4H-SiC, HPSI, Research Grade, 100mm, On-Axis, $\geq 1E5$ ohm-cm, Standard MPD, 500um Thick w/ 32.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4TPFOR-0200	4H-SiC, HPSI, Production Grade, 100mm, On-Axis, $\geq 1E5$ ohm-cm, Standard MPD, 500um Thick w/ 32.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4TRG0R-N-0200	4H-SiC, HPSI, Research Grade, 150mm, On-Axis, $\geq 1E5$ ohm-cm, Standard MPD, 500um Thick w/ Notch, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate
W4TPG0R-N-0200	4H-SiC, HPSI, Production Grade, 150mm, On-Axis, $\geq 1E5$ ohm-cm, Standard MPD, 500um Thick w/ Notch, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate

How to Order



Learn how Wolfspeed can revolutionize your designs at wolfspeed.com/materials or contact us at materials_sales@wolfspeed.com or +1.919.313.5300.

Our materials are ISO-TS 16949 certified. The information in this document is subject to change without notice. Document revised February 15, 2019. © 2019 Cree, Inc. All rights reserved. Wolfspeed™ and the Wolfspeed logo are trademarks of Cree, Inc.

